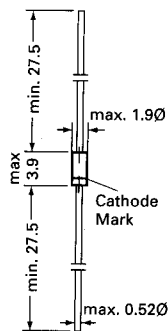


1N 914 ...1N 4454

SILICON EPITAXIAL PLANAR DIODE

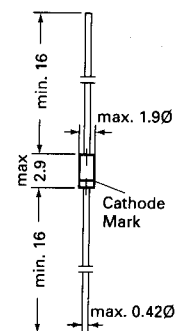
Silicon Epitaxial Planar Diode
for general purpose and switching.

The types 1N4149, 1N4447 and 1N4449 are also available
in glass case DO-34.



Glass case JEDEC DO-35

Dimensions in mm



Glass case JEDEC DO-34

Dimensions in mm

branded on reel
or AMMOPAK

Type	Peak reverse voltage V_{RM} V	Max. aver. rectified current I_o mA	Max. power dissip. at 25 °C P_{tot} mW	Max. junction temperature T_j °C	Max. forward voltage drop		Max. reverse current		Max. reverse recovery time	
					V_F V	at I_F mA	I_R nA	at V_R V	t_{rr} ns	Conditions
1N914	100	75	500	200	1.0	10	25	20	max. 4.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$, to $I_R = 1$ mA
1N4149 ¹⁾	100	150	500	200	1.0	10	25	20	max. 4.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$, to $I_R = 1$ mA
1N4150	50	200	500	200	1.0	200	100	50	max. 4.0	$I_F = I_R = 10$ to 200 mA, to 0.1 I_F
1N4151	75	150	500	200	1.0	50	50	50	max. 2.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$, to $I_R = 1$ mA
1N4152	40	150	400	175	0.55	0.10	50	30	max. 2.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$, to $I_R = 1$ mA
1N4153	75	150	400	175	0.55	0.10	50	50	max. 2.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$, to $I_R = 1$ mA
1N4154	35	150 ²⁾	500	200	1.0	30	100	25	max. 2.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$, to $I_R = 1$ mA
1N4447 ¹⁾	100	150	500	200	1.0	20	25	20	max. 4.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$, to $I_R = 1$ mA
1N4449 ¹⁾	100	150	500	200	1.0	30	25	20	max. 4.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100 \Omega$, to $I_R = 1$ mA
1N4450	40	150	400	175	0.54	0.50	50	30	max. 4.0	$I_F = I_R = 10$ mA, to $I_R = 1$ mA
1N4451	40	150	400	175	0.50	0.10	50	30	max. 10	$I_F = I_R = 10$ mA, to $I_R = 1$ mA
1N4453	30	150	400	175	0.55	0.01	50	20	-	-
1N4454	75	150	400	175	1.0	10	100	50	max. 4.0	$I_F = I_R = 10$ mA, to $I_R = 1$ mA

¹⁾ These diodes are also available in glass case DO-34.

²⁾ Valid provided that leads at a distance of 8mm from case are kept at ambient temperature.

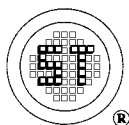
Parameters for diodes in case DO-34:

$$P_{tot} = 300 \text{ mW}$$

$$T_j = 175 \text{ }^\circ\text{C}$$

$$T_s = -65 \text{ to } +175 \text{ }^\circ\text{C}$$

$$R_{thA} = \leq 0.4 \text{ K/mW}$$



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